

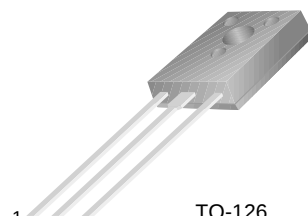
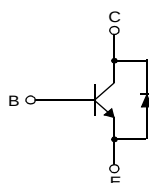
FJE5304D

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High Voltage High Speed Power Switch Application

- Wide Safe Operating Area
- Built-in Free Wheeling diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time

Equivalent Circuit



TO-126
1. Emitter 2. Collector 3. Base

NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current (DC)	4	A
I_{CP}	* Collector Current (Pulse)	8	A
I_B	Base Current (DC)	2	A
I_{BP}	* Base Current (Pulse)	4	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	30	W
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

* Pulse Test Pulse Width = 5ms, Duty Cycle $\geq 1.0\%$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 1\text{mA}, I_E = 0$	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1\text{mA}, I_C = 0$	12			V
I_{CES}	Collector Cut-off Current	$V_{CE} = 700\text{V}, V_{EB} = 0$			100	mA
I_{CEO}	Collector Cut-off Current	$V_{CE} = 400\text{V}, I_B = 0$			250	mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 12\text{V}, I_C = 0$			100	mA
h_{FE}	DC Current Gain	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$ $V_{CE} = 5\text{V}, I_C = 2\text{A}$	10 8		40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2.5\text{A}, I_B = 0.5\text{A}$			0.7 1.0 1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2.5\text{A}, I_B = 0.5\text{A}$			1.1 1.2 1.3	V
V_f	Internal Diode Forward Voltage Drop	$I_F = 2\text{A}$			2.5	V

Electrical Characteristics (Continued) $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	TYP.	Max.	Units
Inductive Load Switching (V _{CC} = 200V)						
t _{stg}	Storage Time	I _C = 2A, I _{B1} = 0.4A V _{BE(off)} = -5V, L = 200μH		0.6		μs
tf	Fall Time			0.1		
Resistive Load Switching (V _{CC} = 250V)						
t _{stg}	Storage Time	I _C = 2A, I _{B1} = I _{B2} = 0.4A T _P = 30μs			2.9	μs
tf	Fall Time			0.2		

* Pulse test: $PW \leq 300\mu\text{s}$, Duty cycle $\leq 2\%$ **Thermal Characteristics** $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.17	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	83.3	$^\circ\text{C/W}$

Typical Characteristics

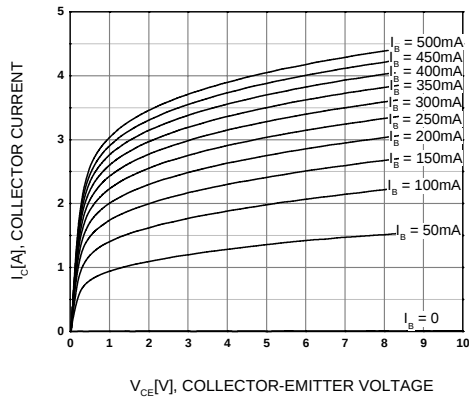


Figure 1. Static Characteristic

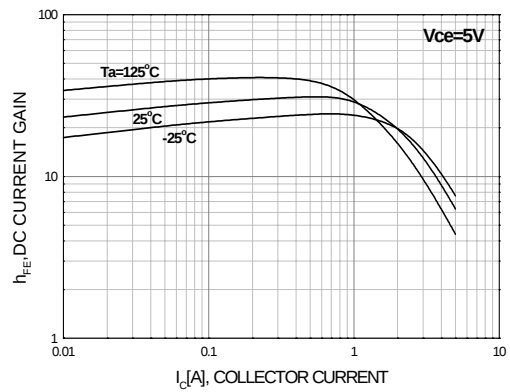


Figure 2. DC Current Gain

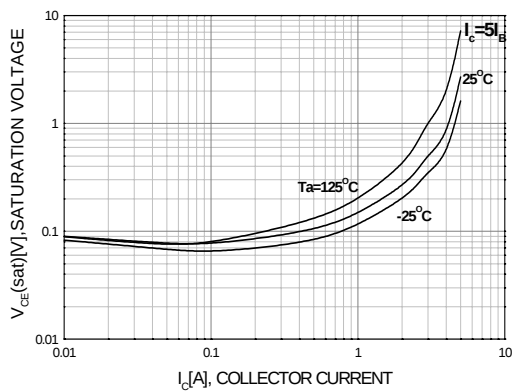


Figure 3. Collector-Emitter Saturation Voltage

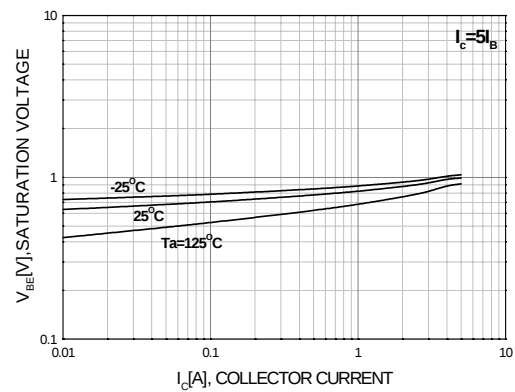


Figure 4. Base-Emitter Saturation Voltage

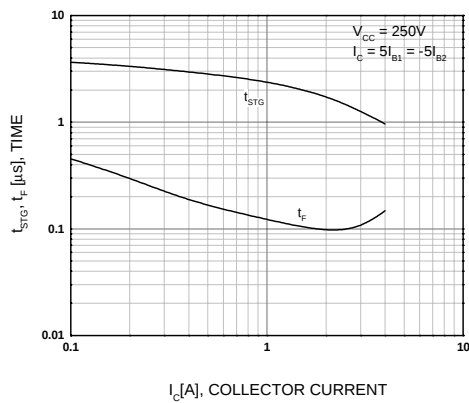


Figure 5. Resistive Load Switching Time

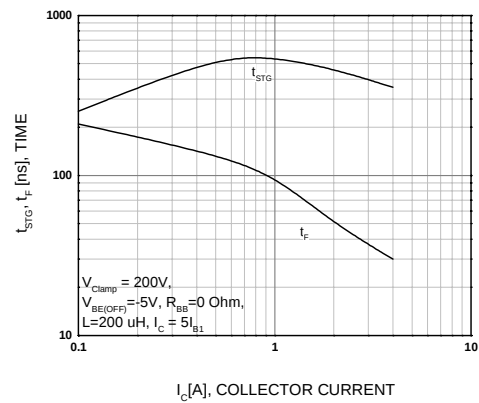


Figure 6. Inductive Load Switching Time

Typical Characteristics (Continued)

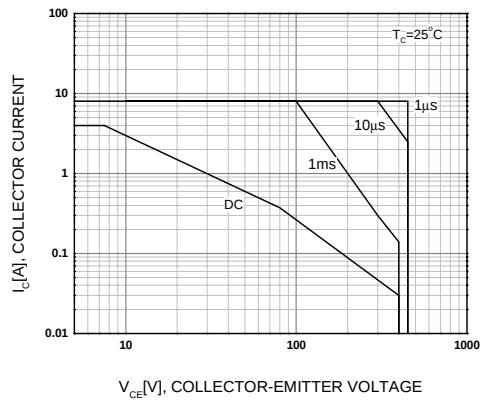


Figure 7. Forward Bias Safe Operating Area

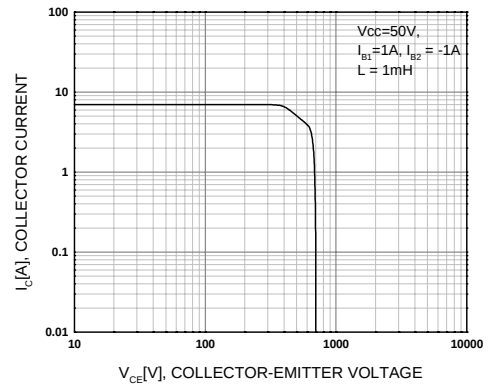


Figure 8. Reverse Bias Safe Operating Area

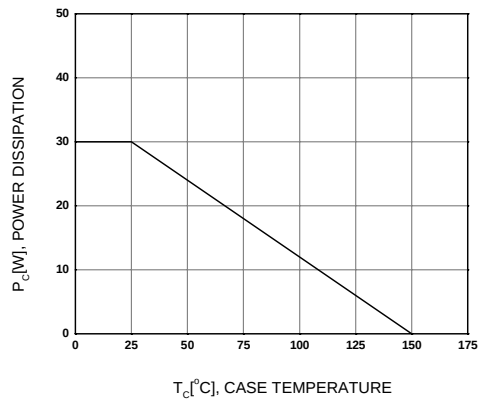
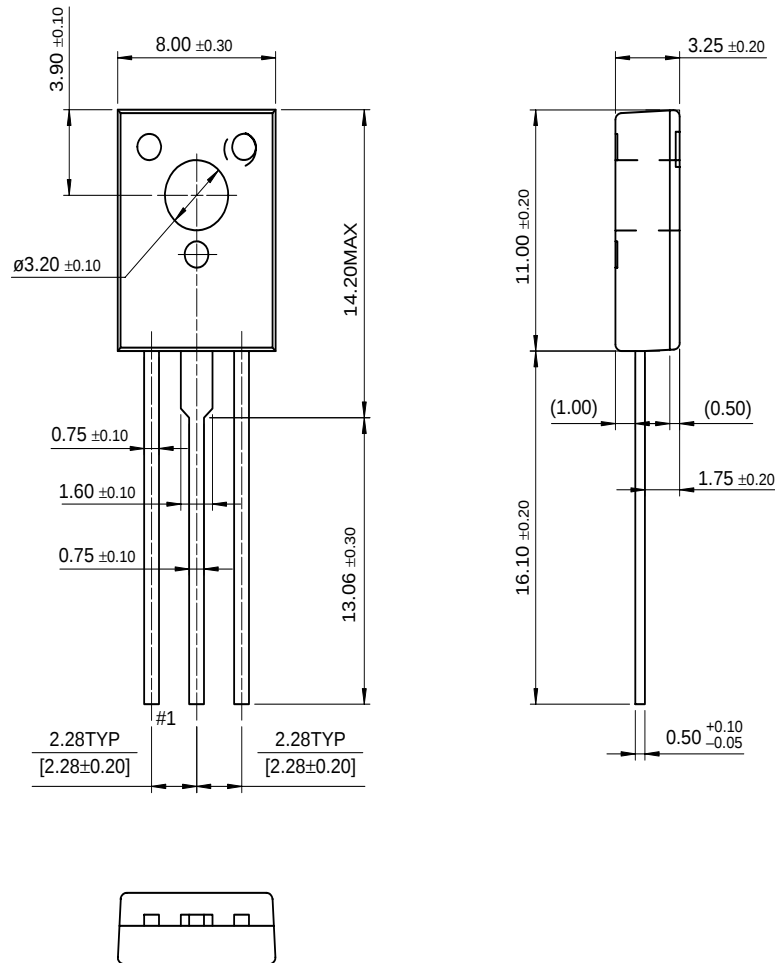


Figure 9. Power Derating

Package Dimensions

TO-126



Dimensions in Millimeters

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DOME TM	GTO TM	MICROWIRE TM	QT Optoelectronics TM	TinyLogic [®]
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